



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

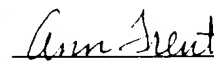
Applicant: Philip L. Hower, et al. ✓ Docket No: TI-30010
Serial No: 10/036,323 Conf. No: 3224
Examiner: Thomas L. Dickey Art Unit: 2826
Filed: 12/31/2001
For: N-CHANNEL LDMOS WITH BURIED P-TYPE REGION TO PREVENT PARASITIC
BIPOLAR EFFECTS

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(a)

I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 6-4-03.


Ann Trent

Dear Sir:

Responsive to the Office Action mailed March 12, 2003, in connection with the above identified application, Applicants respectfully submit the following amendments and remarks.

IN THE SPECIFICATION

Please replace the title with the following rewritten title:

--N-channel LDMOS with buried P-type region to prevent parasitic bipolar effects--

TECHNOLOGY CENTER
JUN 12 2003
MAIL ROOM